

FIG. 1

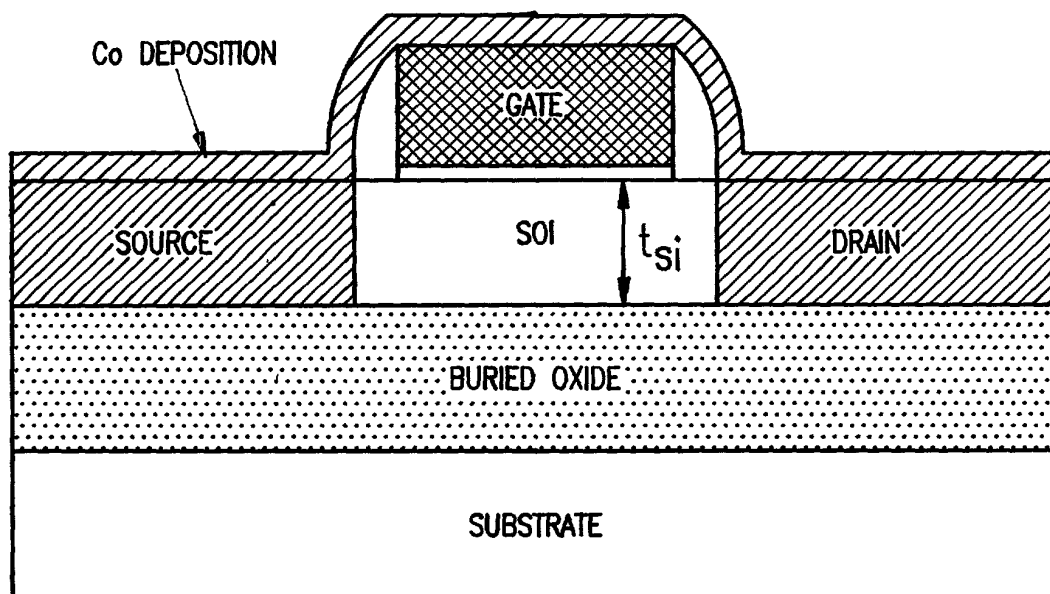


FIG. 2

FIG. 1

FORM Co_2Si BY LOW TEMPERATURE ANNEAL

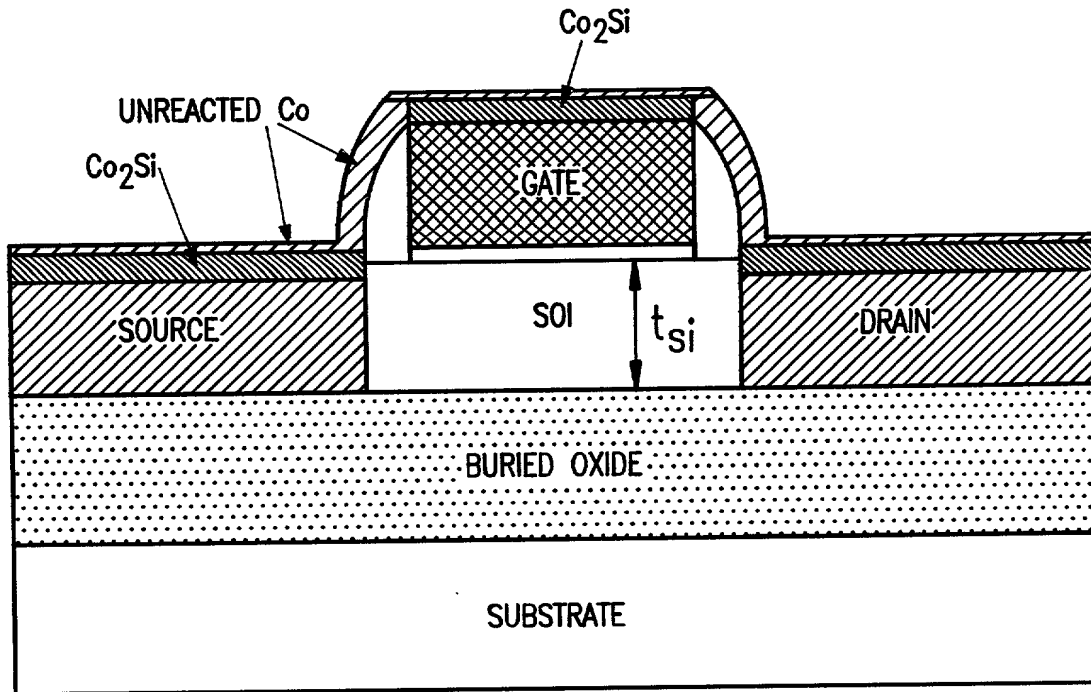


FIG.3

DEPOSITE $\alpha\text{-Si}$

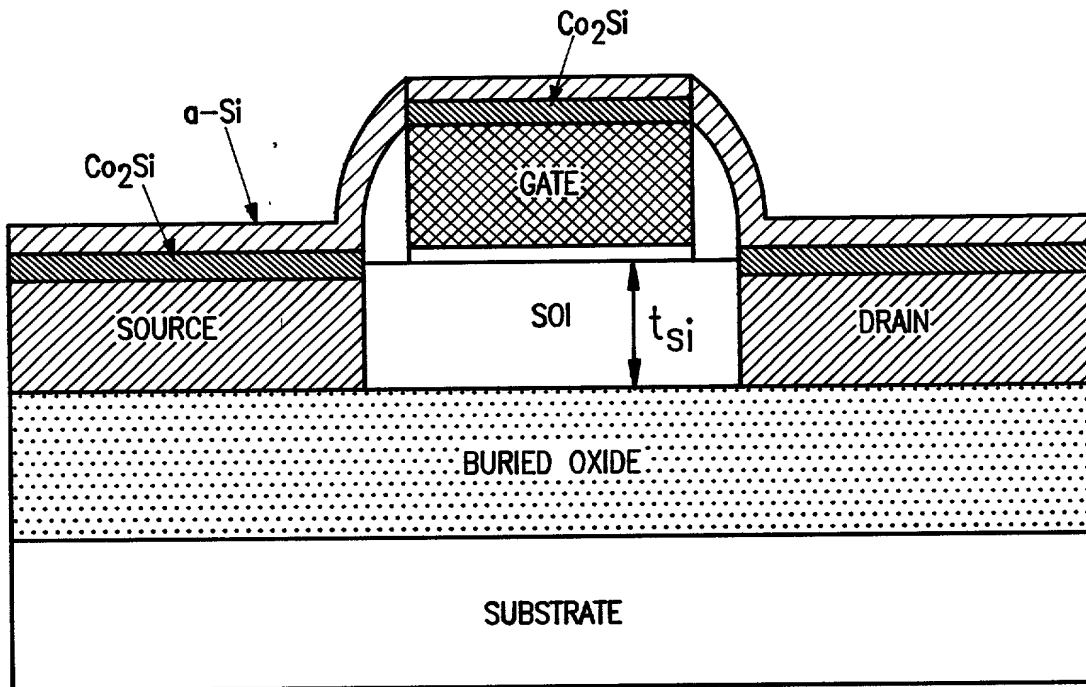


FIG.4

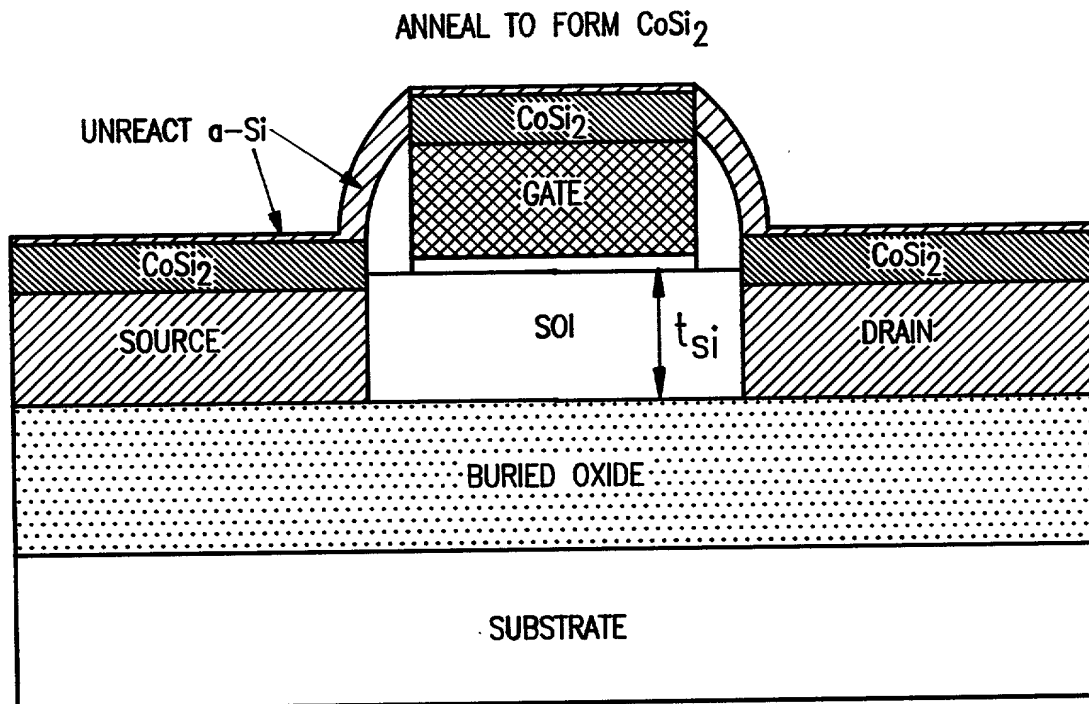


FIG.5

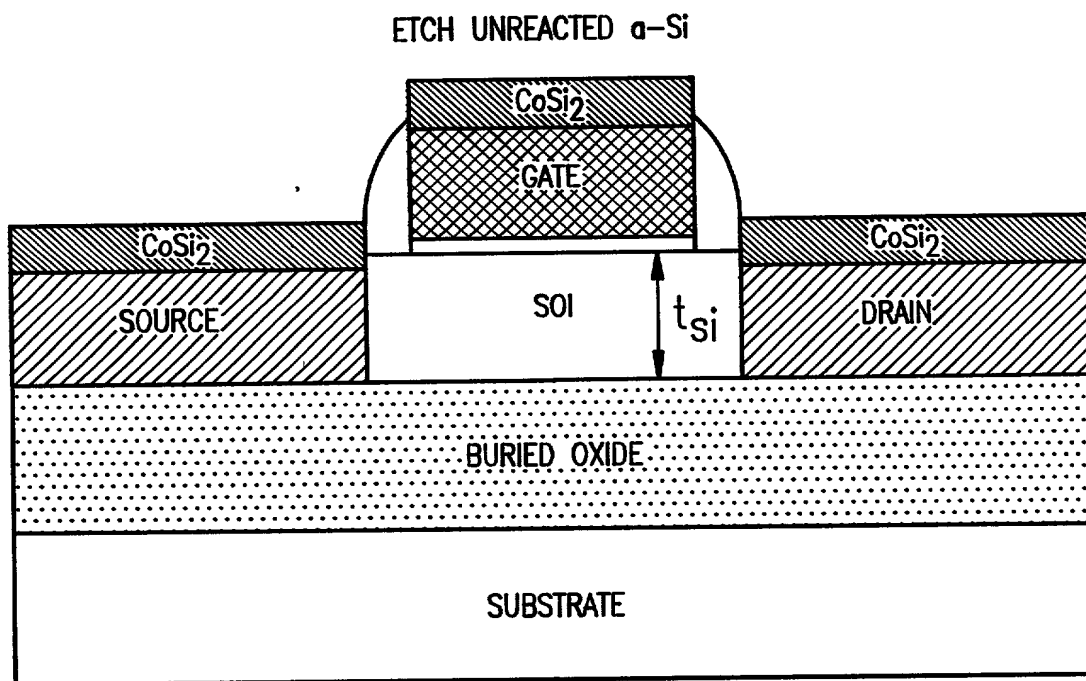


FIG.6

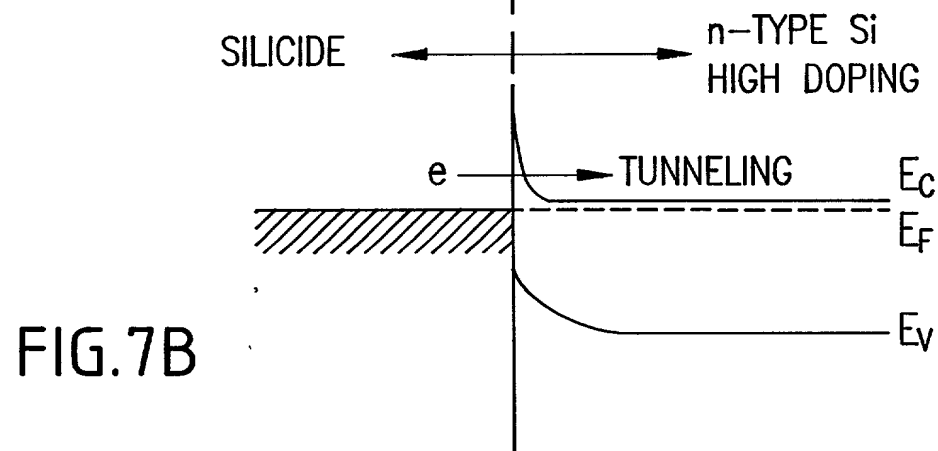
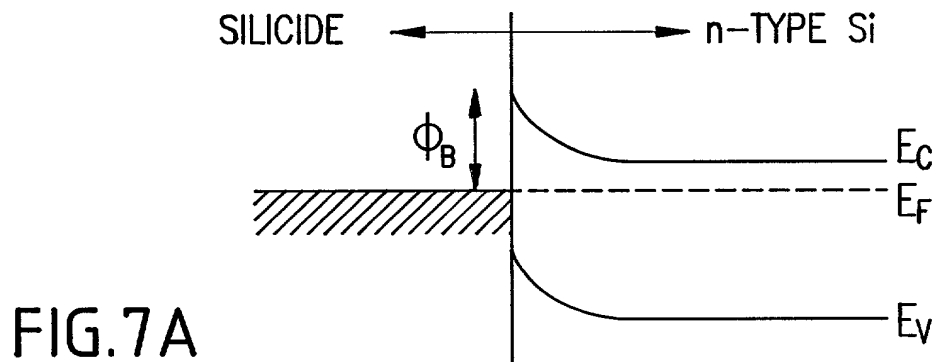
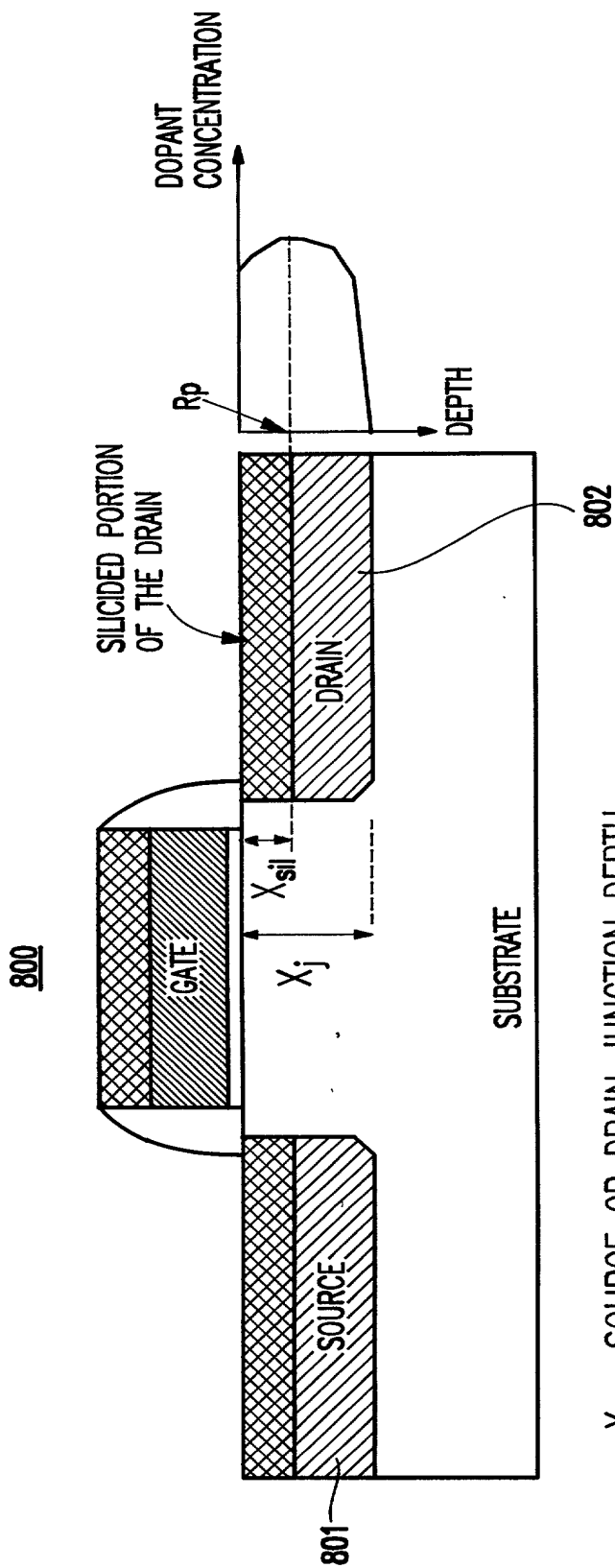


FIG. 8



X_j = SOURCE OR DRAIN JUNCTION DEPTH

X_{sil} = SILICIDE JUNCTION DEPTH

R_p = PEAK DOPANT CONCENTRATION

REQUIREMENTS:

1. $X_j > X_{sil}$
2. X_{sil} ROUGHLY EQUALS R_p

FIG.8

